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Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Input	Forward Current	IF	±60	mA
	Power Dissipation	PD	100	mW
	Power Dissipation Derating factor (above Ta = 100°C)	PDD	2.9	mW/°C
	Thermal Resistance Junction-Ambient	RthJ-A	325	°C/W
	Thermal Resistance Junction-Case	RthJ-C	200	°C/W
Output	Power Dissipation	PC	150	mW
	Collector Current	IC	50	mA
	Collector-Emitter Voltage	VCEO	80	V
	Emitter-Collector Voltage	VECO	7	V

Thermal Characteristics

Parameter	Symbol	Value	Unit
Total Power Dissipation	PTOT	200	mW
Isolation Voltage *1	VISO	5000	Vrms
Operating Temperature	TOPR	-55 ~ +100	°C
Storage Temperature Range	TSTG	-55 ~ +125	°C
Soldering Temperature *2	TSOL	260	°C

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Reflow soldering